

Silicon N-Channel Power MOSFET

Description

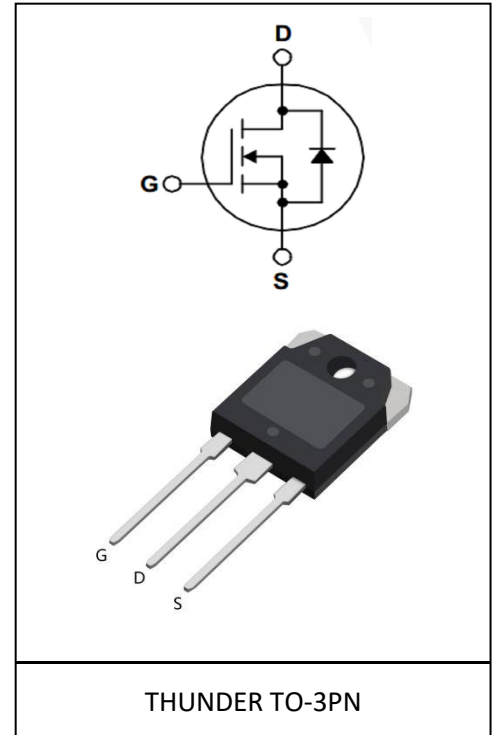
The TH20N65PB uses advanced technology and design to provide excellent $R_{DS(ON)}$. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

General Features

- $V_{DS}=650V, I_D=20A$
- Low ON Resistance
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Application

- Power switching application



Electrical Characteristics @ $T_a=25^\circ\text{C}$ (unless otherwise specified)

a) Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Breakdown Voltage	650	V
I_D	Drain Current (continuous) at $T_c=25^\circ\text{C}$	20	A
I_{DM}	Drain Current (pulsed)	80	A
V_{GS}	Gate to Source Voltage	+/-30	V
P_{tot}	Power Dissipation at $T_c=25^\circ\text{C}$	250	W
	Derating Factor above 25°C	2.0	W/ $^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy	1200	mJ

b) Electrical Parameters:

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{DS}	Drain-source Voltage	$V_{GS}=0V, I_D=250\mu A$	650			V
$R_{DS(on)}$	Static Drain-to-Source on-Resistance	$V_{GS}=10V, I_D=10A$		0.37	0.5	Ω
$V_{GS(th)}$	Gated Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
I_{DSS}	Drain to Source leakage Current	$V_{DS}=600V, V_{GS}=0V$			1.0	μA
$I_{GSS(F)}$	Gated to Source Forward Leakage	$V_{GS}=+30V$			100	nA
$I_{GSS(R)}$	Gated to Source Reverse Leakage	$V_{GS}=-30V$			-100	nA
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ $f=1.0MHz$		2400		pF
C_{oss}	Output Capacitance			225		pF
C_{rss}	Reverse Transfer Capacitance			20		pF

c) Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=325V, I_D=20A,$ $R_G=25\Omega$		35		nS
t_r	Turn-on Rise Time			82		nS
$t_{d(off)}$	Turn-off Delay Time			180		nS
t_f	Turn-off Fall Time			90		nS
Q_g	Total Gate Charge	$V_{DS}=325V$ $I_D=20A$ $V_{GS}=10V$		65		nC
Q_{gs}	Gate-Source Charge			11		nC
Q_{gd}	Gate-Drain Charge			26		nC

d) Source-Drain Diode Characteristics

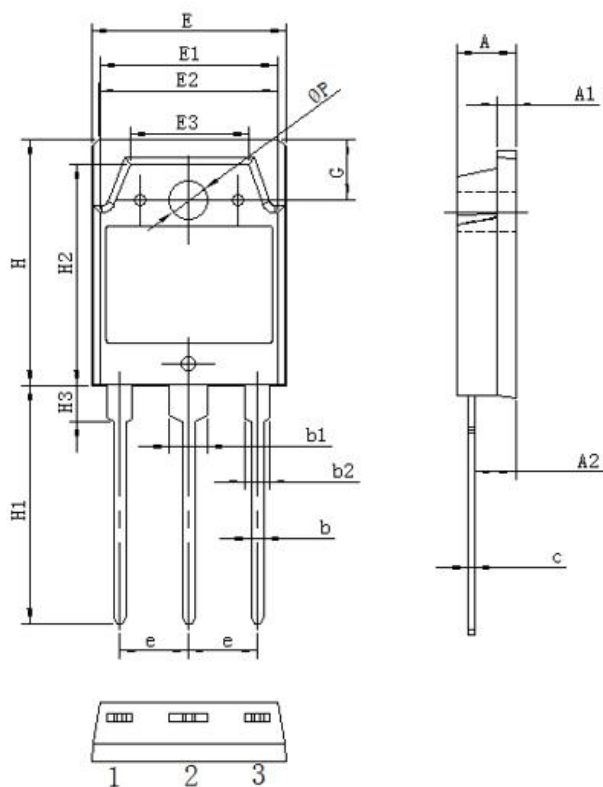
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I _{SD}	S-D Current(Body Diode)				20	A
I _{SDM}	Pulsed S-D Current(Body Diode)				80	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{DS} =20A			1.5	v
t _{rr}	Reverse Recovery Time	T _J =25℃, I _S =20A di/dt=100A/us		390		nS
Q _{rr}	Reverse Recovery Charge			3.4		μC
	*Pulse Test: Pulse Width <= 300μs, Duty Cycle< =2%					

Symbol	Parameter	Typ	Units
$R_{\theta JC}$	Junction-to-Case	0.5	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	40	$^\circ C/W$

Package Information

TO-3PN PACKAGE

基本尺寸



Symbol	单位 mm		
	Min	Nom	Max
A	4.60	4.80	5.00
A1	1.3	1.5	1.7
A2	2.20	2.40	2.60
b	0.80	1.0	1.20
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.2	15.6	16.0
E1	13.2	13.4	13.6
E2	13.1	13.3	13.5
E3	9.1	9.3	9.5
H	19.8	20.0	20.2
H1	19.4	19.8	20.2
H2	18.5	18.7	18.9
H3	2.9	3.1	3.3
G	4.8	5.0	5.2
ΦP	3.00	3.20	3.40

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